



STP190NF04

STB190NF04 - STB190NF04-1

N-channel 40V - 0.0039Ω - 120A - D²PAK/I²PAK/TO-220
STripFET™ III Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STP190NF04	40V	<0.0043Ω	120A
STB190NF04	40V	<0.0043Ω	120A
STB190NF04-1	40V	<0.0043Ω	120A

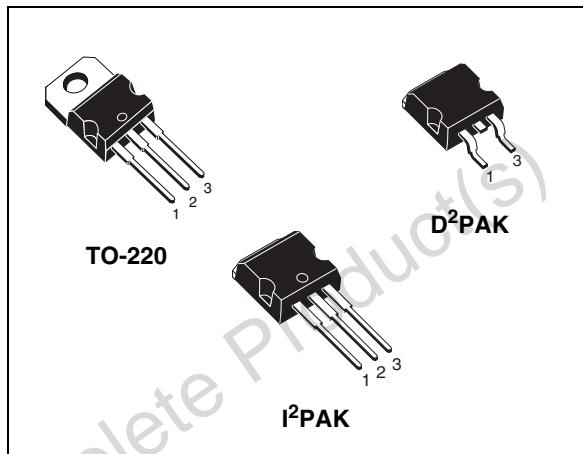
- Standard threshold drive
- 100% avalanche tested

Description

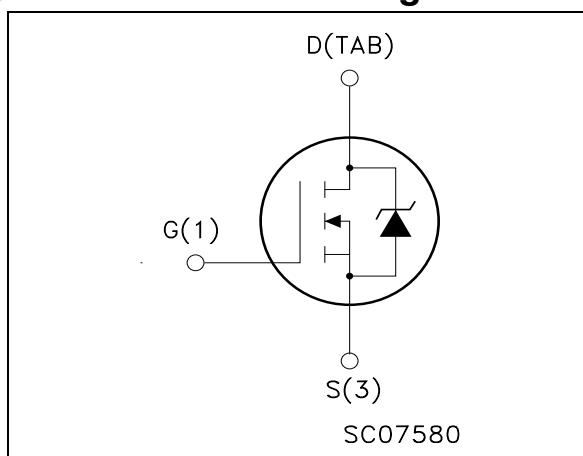
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB190NF04T4	B190NF04	D ² PAK	Tape & reel
STB190NF04-1	B190NF04	I ² PAK	Tube
STP190NF04	P190NF04	TO-220	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	40	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	40	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	310	W
	Derating factor	2.07	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	7	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	860	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Value limited by package
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 190\text{A}$, $dI/dt \leq 600\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
4. Starting $T_j = 25^\circ\text{C}$, $I_D = 95\text{A}$, $V_{DD} = 35\text{V}$

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case max	0.48	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C/W}$
T_J	Maximum lead temperature for soldering purpose ⁽¹⁾	300	$^\circ\text{C}$

1. for 10 sec. 1.6mm from case

2 Electrical characteristics

($T_{CASE}=25^\circ\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}, V_{GS} = 0$	40			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max ratings}$ $V_{DS} = \text{max ratings}, T_C = 125^\circ\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2		4	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10\text{V}, I_D = 95\text{A}$		0.0039	0.0043	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}, I_D = 95\text{A}$		200		s
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}, f = 1\text{MHz}, V_{GS} = 0$		5800 1500 200		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 20\text{V}, I_D = 95\text{A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{V}$ (see Figure 15)		45 380 100 75		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 20\text{V}, I_D = 190\text{A}, V_{GS} = 5\text{V}$ (see Figure 16)		130 40 45		nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				120 480	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120\text{A}$, $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 190\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$, $V_{DD} = 34\text{V}$, $T_j = 150^\circ\text{C}$ (see Figure 17)		90 295 6.5		ns nC A

1. Pulse width limited by safe operating area.
 2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

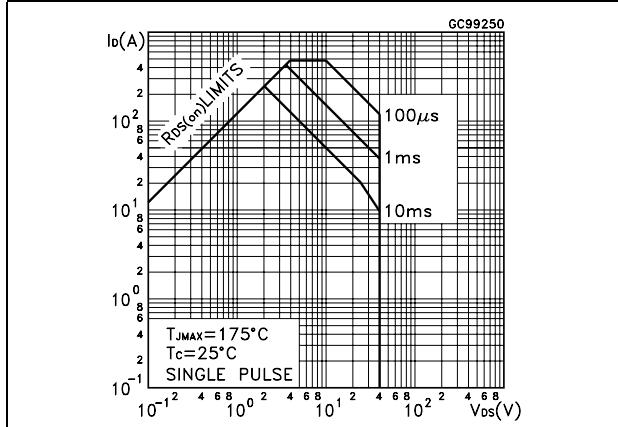


Figure 2. Thermal impedance

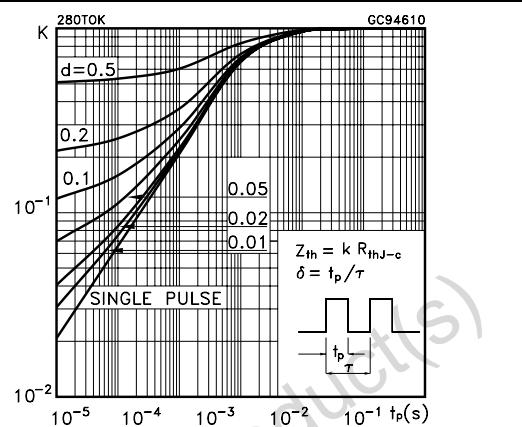


Figure 3. Output characteristics

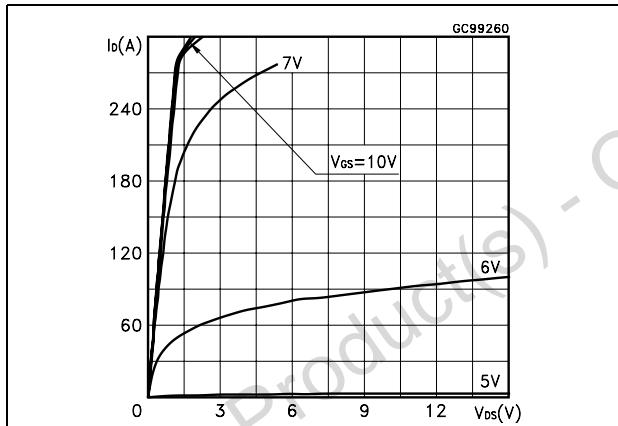


Figure 4. Transfer characteristics

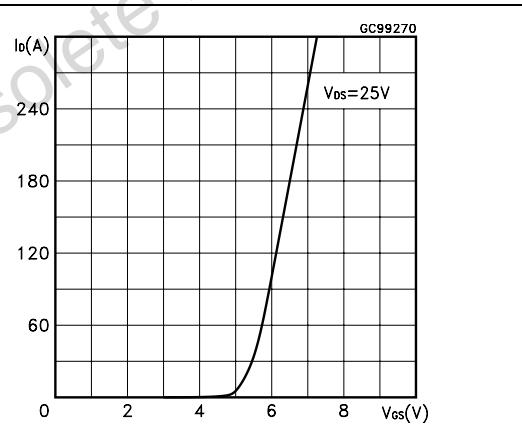


Figure 5. Transconductance

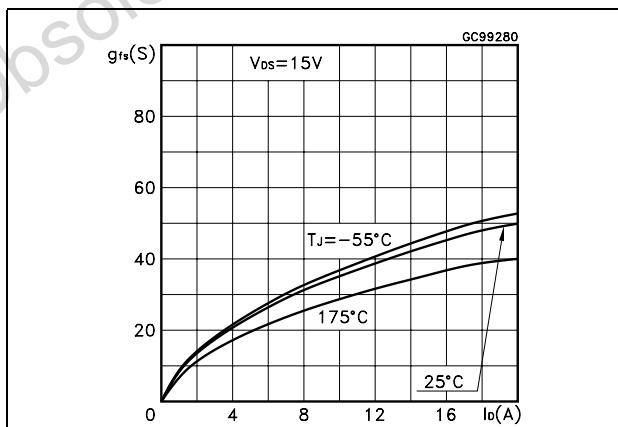


Figure 6. Static drain-source on resistance

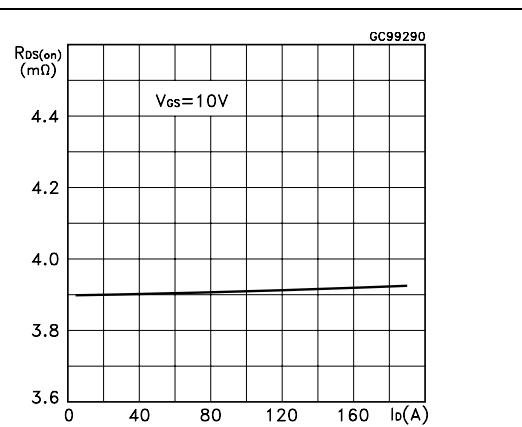


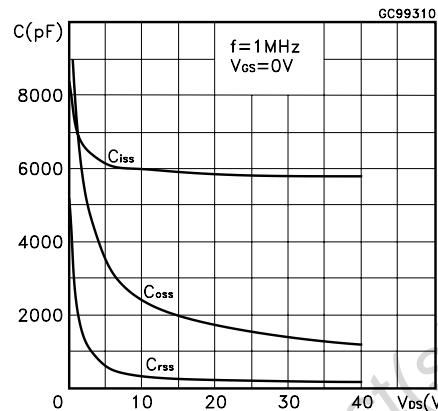
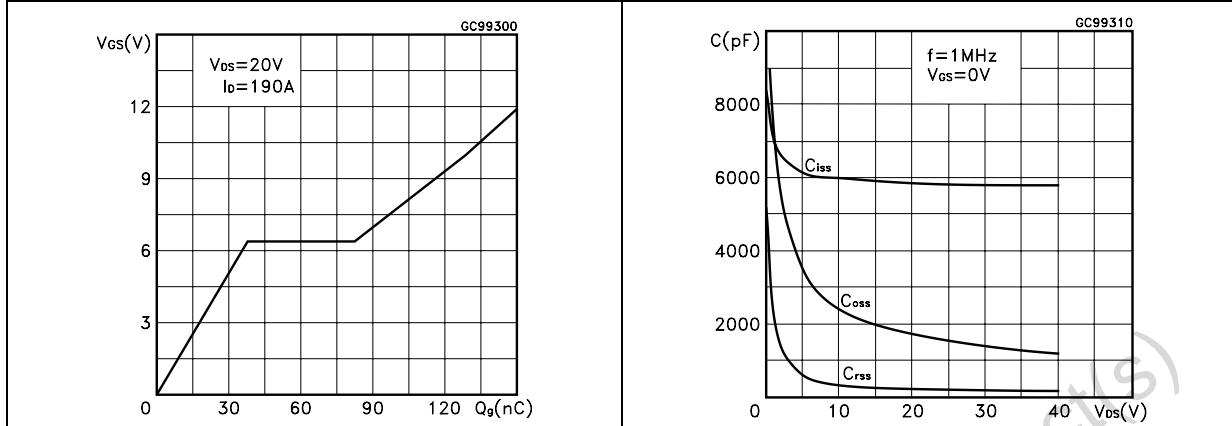
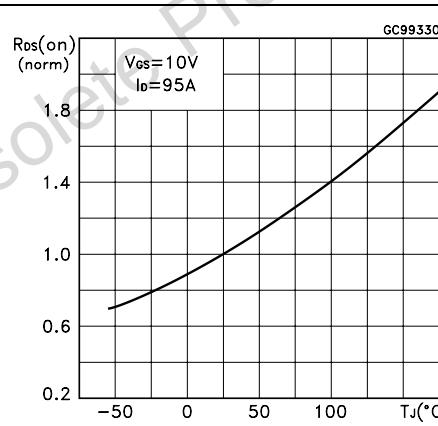
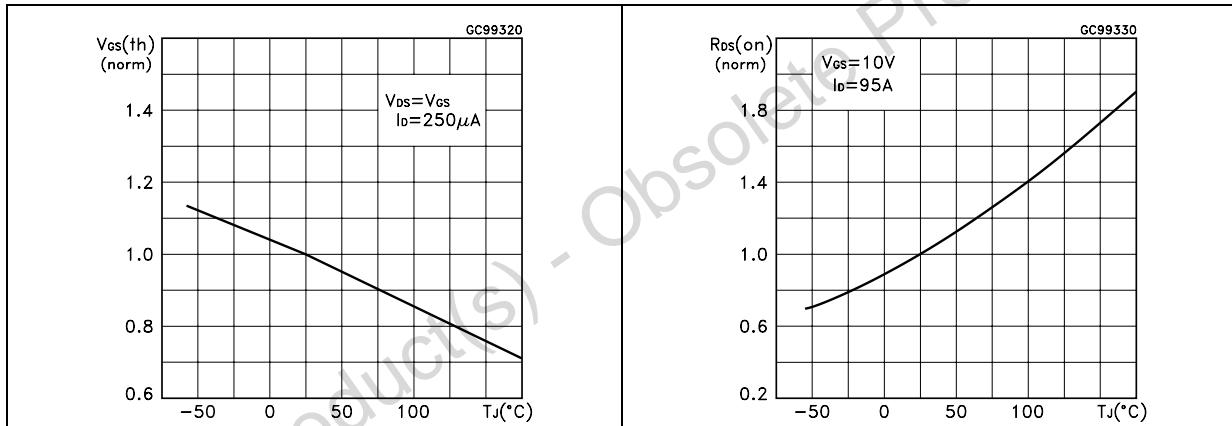
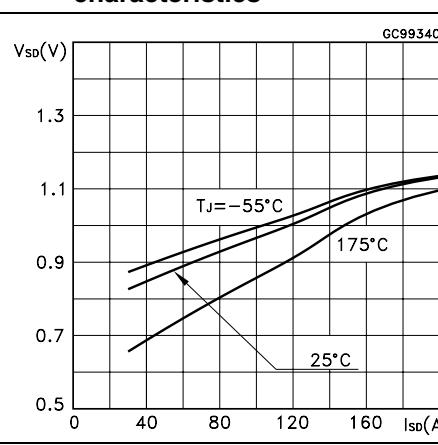
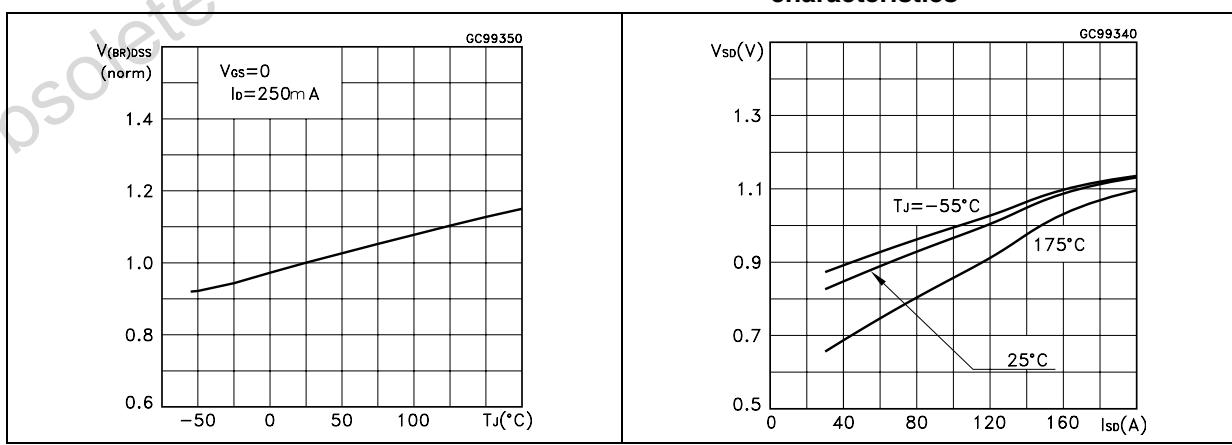
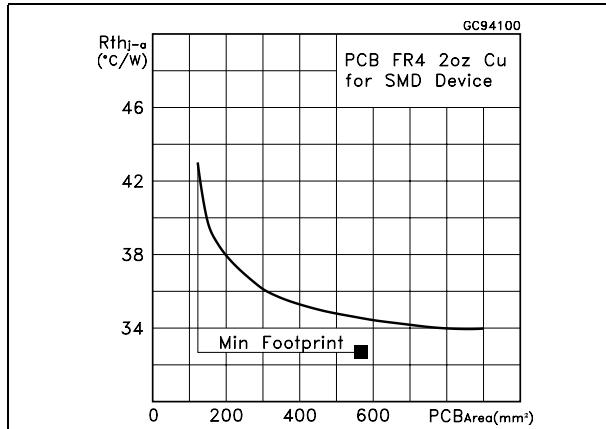
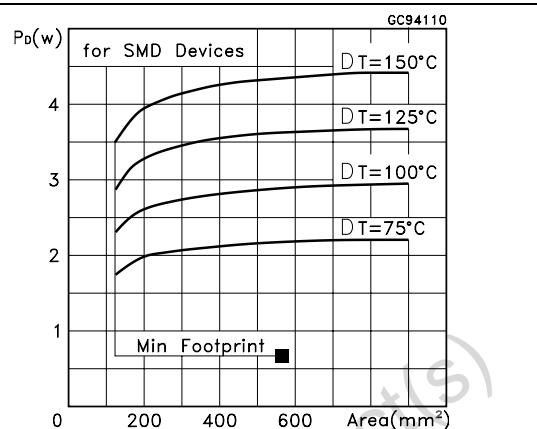
Figure 7. Gate charge vs gate-source voltage **Figure 8.** Capacitance variations**Figure 9.** Normalized gate threshold voltage vs temperature**Figure 10.** Normalized on resistance vs temperature**Figure 11.** Normalized B_{VDSS} vs temperature**Figure 12.** Source-drain diode forward characteristics

Figure 13. Thermal resistance r_{thj-a} vs PCB copper area**Figure 14. Max power dissipation vs PCB copper area**

3 Test circuit

Figure 15. Switching times test circuit for resistive load

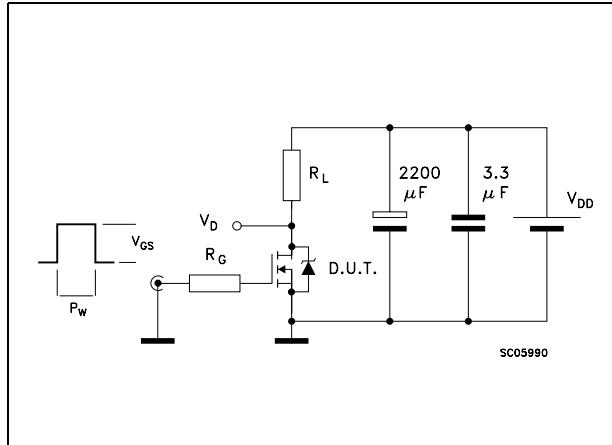


Figure 16. Gate charge test circuit

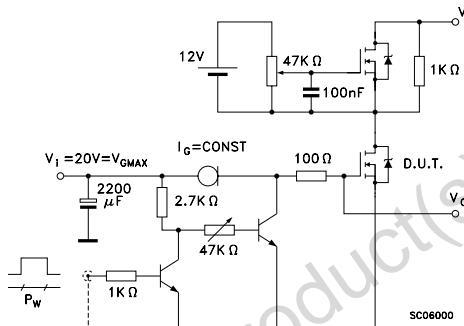


Figure 17. Test circuit for inductive load switching and diode recovery times

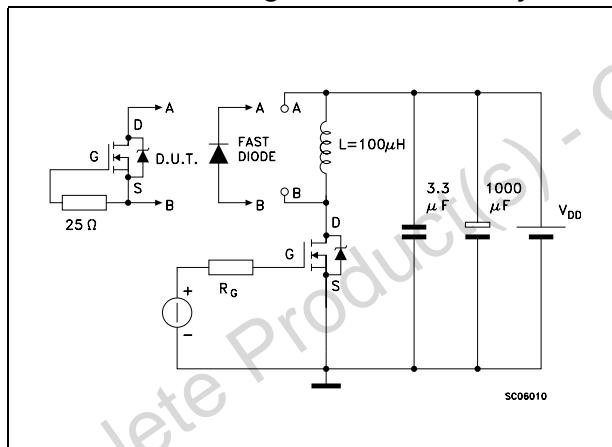


Figure 18. Unclamped Inductive load test circuit

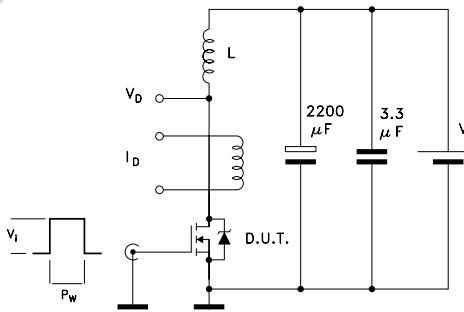


Figure 19. Unclamped inductive waveform

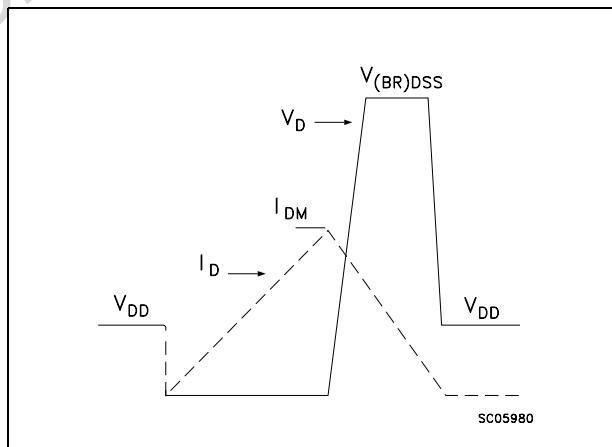
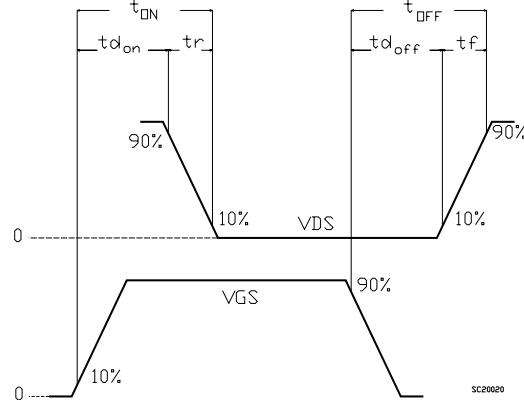


Figure 20. Switching time waveform

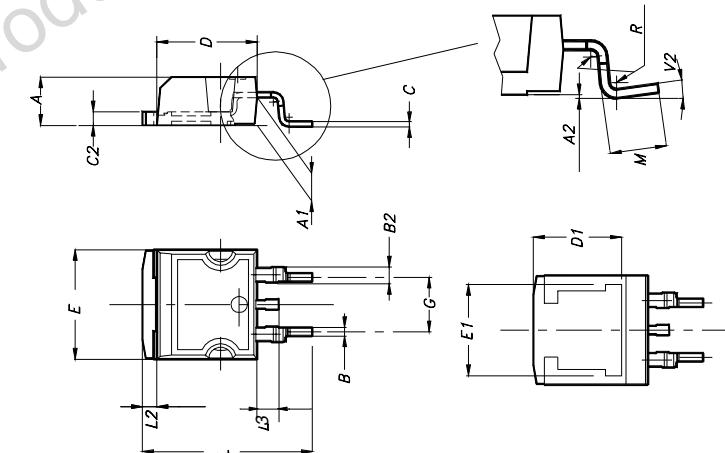


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

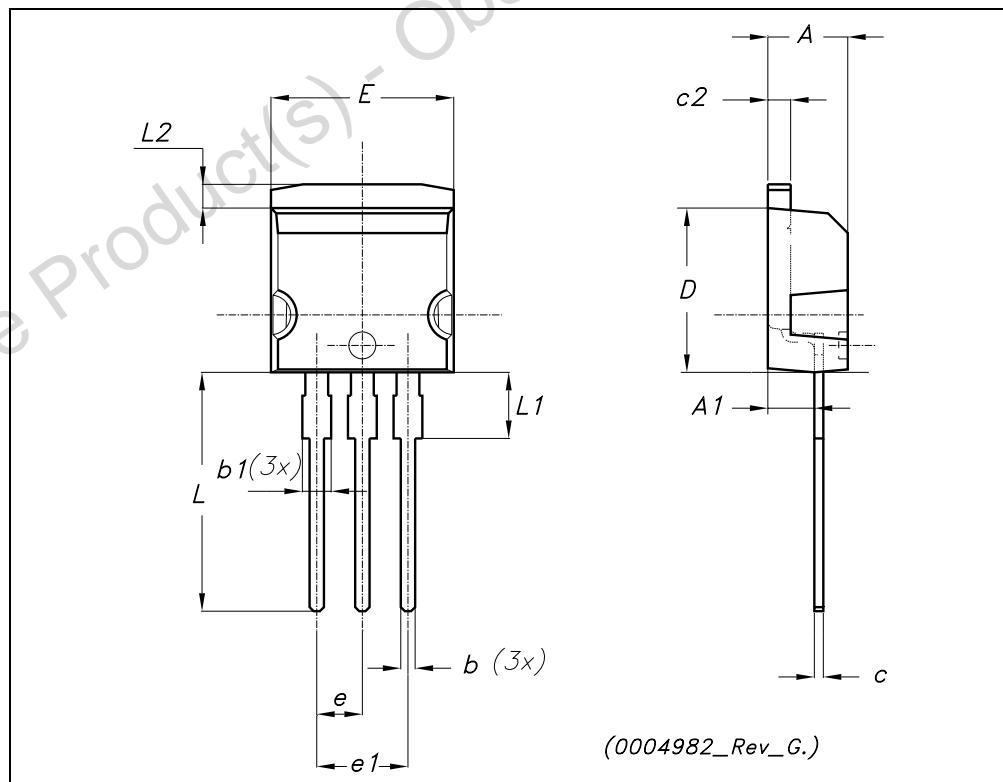
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



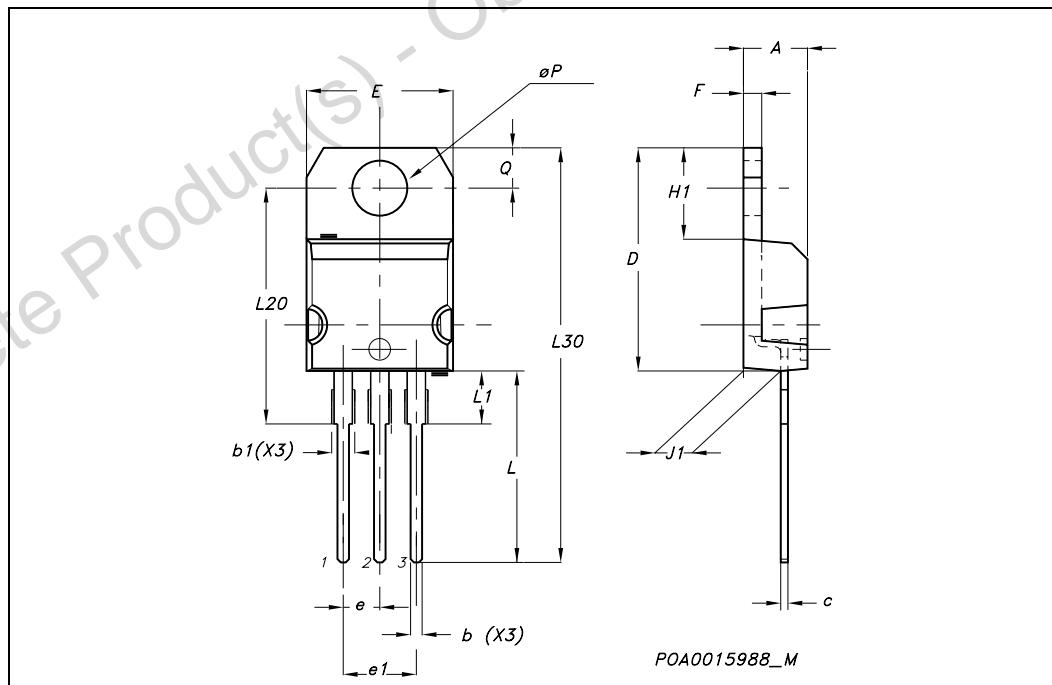
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

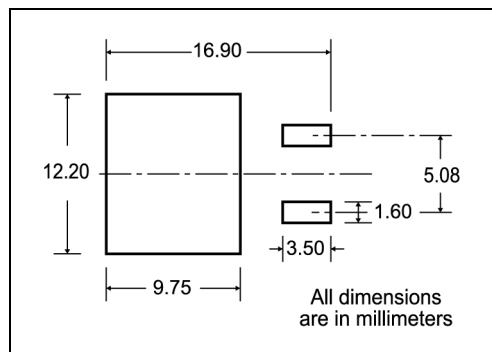


TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



5 Packaging mechanical data

D²PAK FOOTPRINT**TAPE AND REEL SHIPMENT**

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A			330	12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197
BASE QTY		BULK QTY		
1000		1000		

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

* on sales type

6 Revision history

Table 6. Revision history

Date	Revision	Changes
09-Sep-2004	1	First version
09-Aug-2006	2	New template, no content change

Obsolete Product(s) - Obsolete Product(s)

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